

MMBT3904C SOT-883 Silicon General Purpose Transistor (NPN)

General description

SOT-883 Silicon General Purpose Transistor (NPN)

FEATURES

- · Simplifies Circuit Design
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.001g

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

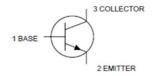
Symbol	Parameter	Value	Units
Vcbo	Collector-Base Voltage	60	V
Vceo	Collector-Emitter Voltage	40	V
VEBO	Emitter-Base Voltage	6	V
$I_{\rm C}$	Collector Current	200	mA
P_{D}	Power Dissipation (FR-4 Board – minimum pad 25°C)	200	mW
RθJA	Thermal Resistance from Junction to Ambient	500	°C /W
Tj Tstg	Junction & Storage Temperature Range	-55 to +150	°C

Green Product



SOT-883 (DFN1006-3)

Electrical Symbol:



Device Marking Code:

Device Type	Marking	Shipping
ММВТ3904С	c 1N B	10,000/Reel

. Off Characteristics

Symbol	Parameter	T C. 1'.'	Limits		Unit
		Test Condition	Min	Max	
V(BR)CEO	Collector-Emitter Breakdown Voltage (Note 1)	$I_C=1$ mA, $I_B=0$ A	40	-	Volts
V(BR)CBO	Collector-Base Breakdown Voltage	$I_C=10uA, I_E=0A$	60	-	Volts
V(BR)EBO	Emitter-Base Breakdown Voltage	$I_{E} = 10uA, I_{B} = 0A$	6	-	Volts
Ісво	Collector Cutoff Current	$V_{CB} = 60V, I_E = 0A$	-	0.1	uA
Icex	Collector Cutoff Current	$V_{CE}=30V$, $V_{EB}=3V$	-	50	nA
Іево	Emitter Cutoff Current	V _{EB} = 5V , I _C =0A		0.1	uA

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%

MMBT3904C



On Characteristics

C 1 1	Parameter	T. (C. IV	Limits		Unit
Symbol		Test Condition	Min	Max	
		$I_{C} = 0.1 \text{mA}, V_{CE} = 1 \text{V}$	40	-	
	DC Current Dain	$I_C=1.0$ mA, $V_{CE}=1$ V	70	-	
H_{FE}		$I_C=10$ mA, $V_{CE}=1$ V	100	300	-
		I_C =50mA, V_{CE} =1V	60	-	
		$I_C=100$ mA, $V_{CE}=1$ V	30	-	
V	Collector-Emitter Saturation Voltage	$I_C=10\text{mA}, I_B=1\text{mA}$	-	0.2	37-14-
VCE(sat)		$I_C=50\text{mA}, I_B=5\text{mA}$	-	0.3	Volts
VBE(sat)	Base-Emitter Saturation Voltage	$I_C=10\text{mA}, I_B=1\text{mA}$	0.65	0.85	37-14-
		I _C =50mA, I _B =5mA	-	0.95	Volts

Small-signal Characteristics

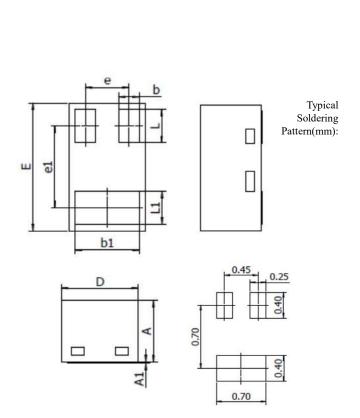
	Parameter		Limits		
Symbol		Test Condition			Unit
			Min	Max	
f_{T}	Current-Gain-Bandwidth Product	$I_C = 10$ mA, $V_{CE} = 20$ V, $f = 100$ MHz	200	-	MHz
Cobo	Output Capacitance	$V_{CB}=5V, I_{E}=0A, f=1.0MHz$	-	4	pF
Cibo	Input Capacitance	$V_{BE} = 0.5V, I_{C} = 0A, f = 1.0MHz$	-	8	pF
h _{ie}	Input Impedancen	$V_{CE}=10V, I_{C}=1mA, f=1.0kHz$	1	10	kΩ
h _{re}	Voltage Feedback Ratio	$V_{CE}=10V, I_{C}=1mA, f=1.0kHz$	0.5	8	X10 ⁻⁴
h _{fe}	Small-signal Current Gain	$V_{CE}=10V, I_{C}=1mA, f=1.0kHz$	100	400	-
hoe	Output Admittance	$V_{CE} = 10V$, $I_{C} = 1$ mA, $f = 1.0$ kHz	1	40	θmhos
NF	Noise Figure	$V_{CE} = 5V, I_{C} = 100uA$		5	dB
141		$Rs=1.0k\Omega f = 1.0kHz$			

Switching Characteristics

		Limits		nits	
Symbol	Parameter	Test Condition	Min	Max	Unit
t d	Delay Time	$V_{CC} = 3V, V_{BE} = 0.5V,$	-	35	
$t_{\rm r}$	Rise Time	$I_C=10\text{mA}, I_{B1}=1\text{mA}$	-	35	nS
ts	Storage Time	V _{CC} =3V, I _C =10mA,	-	200	
t f	Fall Time	$I_{B1} = I_{B2} = 1 \text{mA}$	-	50	nS



SOT-883 Package Outline



	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	0.46	0.50	0.018	0.020
A1		0.03		0.001
D	0.55	0.65	0.022	0.026
Е	0.95	1.05	0.037	0.041
b	0.12	0.22	0.005	0.008
b1	0.45	0.55	0.018	0.022
L	0.22	0.32	0.008	0.013
L1	0.22	0.32	0.008	0.013
e	Тур. 0.34		Тур. 0.013	
el	Тур. 0.65		Тур. 0.026	



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